

<b>SPEC SHEET (FOR REFERENCE)</b>	SHEET No.	Rev.	Page.
	<b>G05014</b>		1 of 1

TYPE : 6PT1003N1T\*\*

CHIP SIZE	1.1 * 1.1 mm
WAFER SIZE	6 inch
POSSIBLE DIE PER WAFER	12,650 pcs

Maximum Ratings(Ta=25°C)

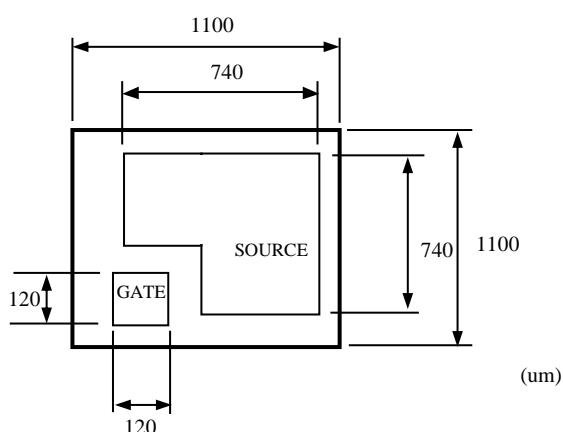
Characteristics	Symbol	Ratings	Unit
Drain-source voltage	VDSS	30	V
Gate-source voltage	VGSS	±8	V
Drain Current (DC)	ID	4	A

\* For Reference

WAFER PROBING SPEC (Ta=25°C)

No	MODE	LIMIT				CONDITIONS
		MIN.	Typ	MAX.	UNIT	
1	IGSS			±1	uA	VGS=±8V VDS=0V
2	IDSS			500	nA	VDS=30V VGS=0V
3	BVDSS	33			V	ID=100uA
4	VTH	0.53		1.0	V	ID=1mA VDS=10V
5	RDS(on)1		35	50	mΩ	ID=2A VGS=4.5V
6	RDS(on)2		45	65	mΩ	ID=2A VGS=2.5V
7	RDS(on)3		80	120	mΩ	ID=0.5A VGS=1.8V
8	VSD		0.85	1.1	V	I=2A VGS=0V
9	Yfs		4		S	Vds=10V Id=0.5A

※ Built-in ZD between Gate and Source.



TENTATIVE

NOTE: